

Replacement Paragraph Page 5, Lines 1-3

A specific object of the invention is to provide for a method and an apparatus for affinity viscometry using ~~measuring, by affinity, the viscosity of~~ very small quantities of highly viscous fluids and for deriving signals thereof.

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Replacement Paragraph Page 5, Lines 9-12

In the accomplishment of these and other objects, the invention, ~~in general~~, provides for a sensor for viscosity affinity measurements of in small fluid volumes without fluid consumption, and for methods of the fabrication of a viscometric a miniaturized sensor suitable for carrying out such measurements, including affinity viscometry.

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Replacement Paragraph Page 8, Lines 4-7

In an alternate embodiment of the invention, at least one moveable cantilevered conductor is positioned in the effective field of a permanent magnet such that the flux lines thereof extend substantially normal to the main directional movement of the conductor.

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Replacement Paragraph Page 9, Line 4

Fig. 2 is a sectional view on an enlarged scale along line II - II of Fig. 1.

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Replacement Paragraph Page 11, Lines 13-22

As regards the fabrication of the apparatus described, the structuring of the measuring zone and the movable loop 3 is significant. In accordance with the invention, the movable loop 3 is fabricated only after formation of all active and passive components of the integrated circuit of the viscosity sensor has been completed, by applying an additional photo lithographically structured lacquer resist mask prior to opening the ~~passivation windows and separation of~~ separating the sensor chips produced on a semiconductor substrate (wafer). The mask serves, ~~to undercut~~ by a localized isotropic insulator etching process, ~~and to undercut and~~ completely separate from the insulating support, the ~~uppermost~~ portion of the conductor plane which in the completed sensor constitutes the resiliently moveable loop 3.

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Replacement Paragraph Page 12, Lines 1-6

This may be accomplished by the upper partial layer 10 of the intermediate insulator consisting of silicon dioxide or silicate glass and a lower partial layer 11 consisting of Si_3N_4 . The windows in the passivation layer 12 which also consist of Si_3N_4 , which have been structured with the above-mentioned additional ~~lacquer~~ resist mask prior to the isotropic undercutting, serve as an etching mask.

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